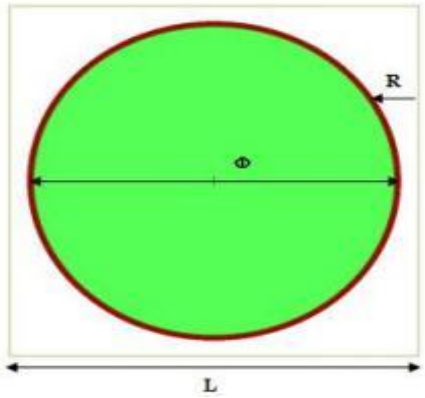
6.75mm×6.75 mm Silicon PIN PD Chip datasheet

P/N：WS88-01C



Feature

Si PIN photodiode chip

Structure

Planar type：PIN diode

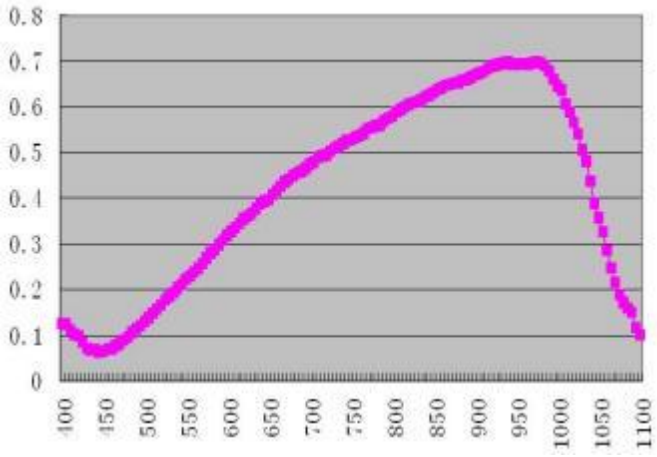
DIMENSIONS

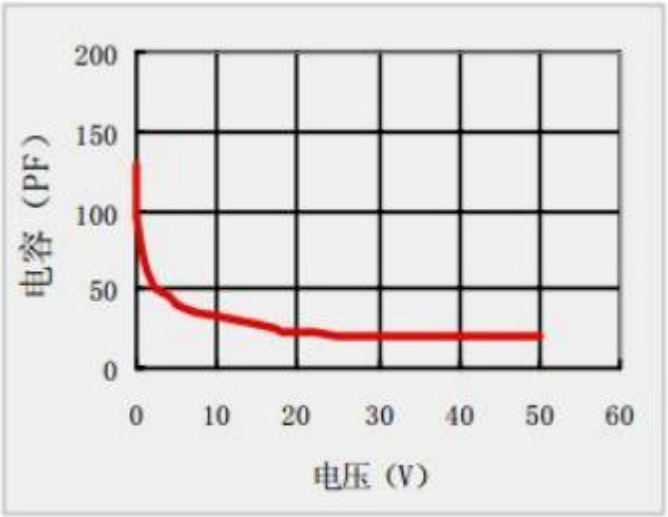
Conditions	Min.	Typ.	Max.	Unit
Active		6.0		mm
Die Thickness		200±10		μm
Bond Pad Radius		110		μm
Size		6.75×6.75		mm
P metal (Ti/Al)		1.2		μm
N metal (Au)		1.0		μm
Note: The structure of PIN PD is planar and front illuminated with P electrode on the top and N electrode on the bottom.				

Electro-Optical Characteristics (@ Ta＝22±3℃)

Parameters	Sym.	Test conditions	Min	Typ	Max	Unit
Response Spectrum	λ	-	400 ~1100			nm
Active Size	Φ	-	6.0			mm
Reponsivity	Re	λ＝900nm, V_R＝15V	-	0.60	0.65	A/W
Response time	tr	λ＝850nm, V_R＝15V, R_L＝50Ω	-	15	30	ns
Forward Voltage	V_F	I_F＝1mA	-	-	0.70	V
Reverse Breakdown Voltage	V_{BR}	I_D＝10μA	120	-	-	V
Dark Current	I_D	V_R＝15V	-	2.0	10.0	nA
Capacitance	C_{PD}	V_R＝15V, f=1MHz	-	35	50	pF

Typical Performance Curves （@Ta＝22±3℃)





Absolute Maximum Rating

Parameter	Symbol	Rating	Unit
Operating temperature	T_C	-40～+55	℃
Storage temperature	T_{STG}	-50～+100	℃